



晶体管 TRANSISTOR A1013A

主要参数 MAIN CHARACTERISTICS

I _c	-1.0A
V _{CEO}	-160V
P _c	900mW

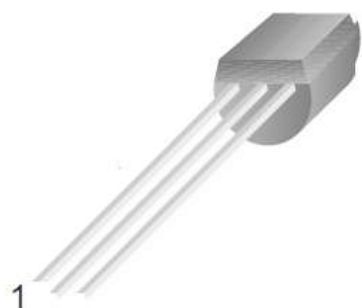
产品特性 FEATURES

硅外延	Epitaxial silicon
高开关速度	High switching speed
与 C2383A 互补	Complementary to C2383A
RoHS 产品	RoHS product

用途 APPLICATIONS

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

封装形式 Package



TO-92LS

1. Emitter 2. Collector 3. Base

绝对最大额定值 ABSOLUTE RATINGS (T_c=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
集电极—基极直流电压 Collector- Base Voltage (I _E =0)	V _{CB0}	-160	V
集电极—发射极直流电压 Collector- Emitter Voltage (I _B =0)	V _{CEO}	-160	V
发射极—基极直流电压 Emitter-Base Voltage (I _C =0)	V _{EB0}	-6.0	V
最大集电极直流电流 Collector Current (DC)	I _c	-1	A
最大集电极耗散功率 Total Dissipation (TO-92)	P _c	900	mW
最高结温 Junction Temperature	T _j	150	°C
贮存温度 Storage Temperature	T _{stg}	-55~+150	°C

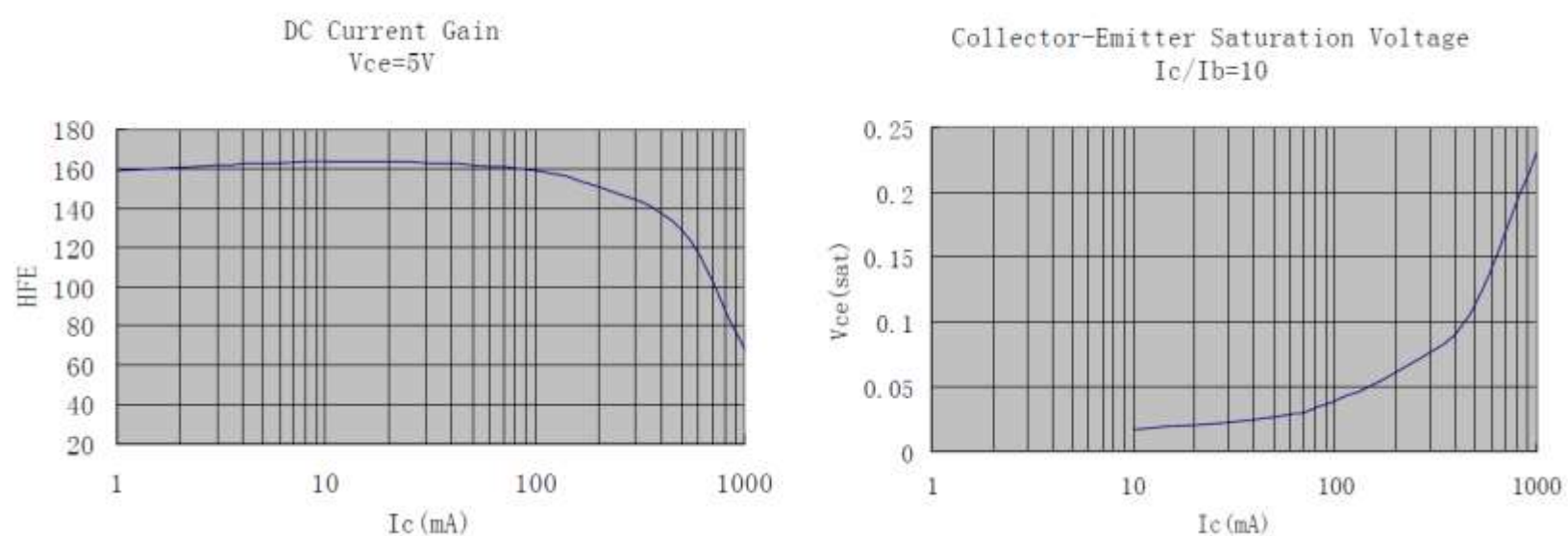
电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
$V(BR)_{CBO}$	$I_C = -100\mu A, I_E = 0$	-160	-	-	V
$V(BR)_{CEO}$	$I_C = -1.0mA, I_B = 0$	-160	-	-	V
$V(BR)_{EBO}$	$I_E = -100\mu A, I_C = 0$	-6.0	-	-	V
I_{CBO}	$V_{CB} = -150V, I_E = 0$	-	-	-1	μA
I_{EBO}	$V_{BE} = -6V, I_C = 0$	-	-	-1	μA
$h_{FE} (1)$	$V_{CE} = -5V, I_C = -10mA$	60	-	320	-
$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-1.5	V
$V_{BE(sat)}$	$V_{CE} = -5V, I_C = -5.0mA$	-	-	-0.75	V
f_T	$V_{CE} = -5V, I_C = -200mA$	15	-	-	MHz

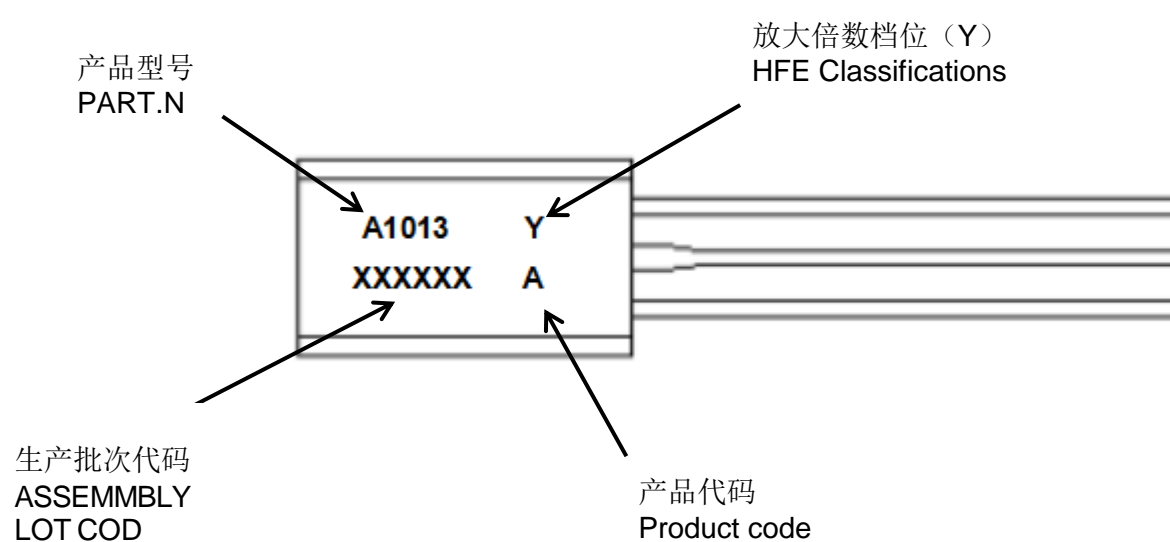
放大倍数 h_{FE} Classifications

h_{FE} Classifications	R	O	Y
h_{FE} Range	60-120	100-200	160-320

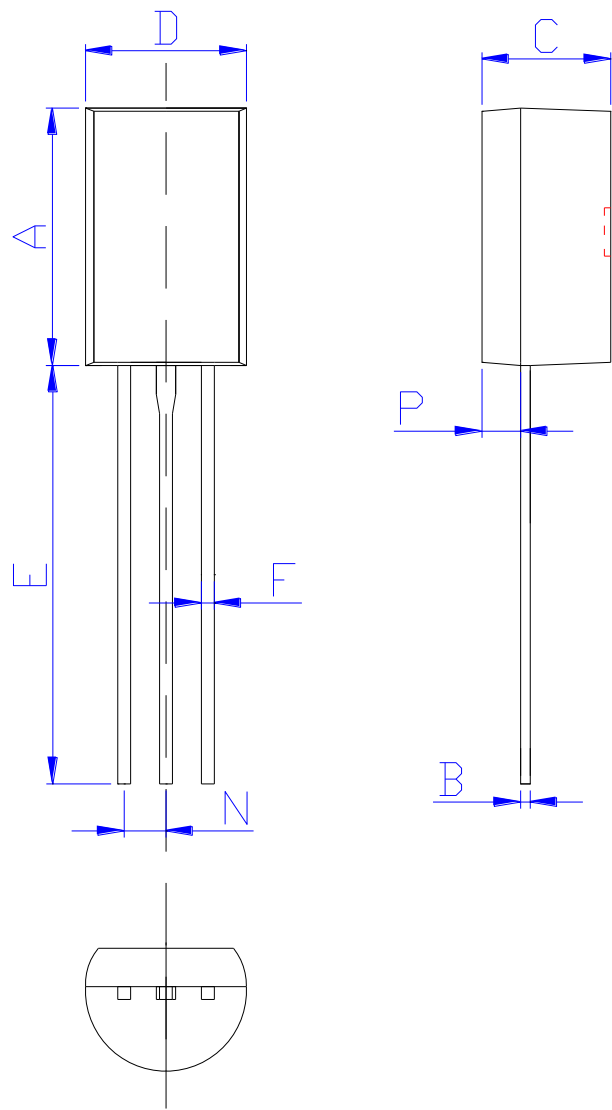
典型特性曲线 Electrical Characteristics



印记 Marking:



外形尺寸: Package Dimension



DIM	MILLIMETERS
A	8.00 ± 0.30
B	0.40 ± 0.25
C	3.80 ± 0.30
D	4.90 ± 0.30
E	13.50 ± 0.30
F	0.50 ± 0.15
N	1.22 ± 0.25
P	1.40 ± 0.30

(Units: mm)